

Abstract of the Disclosure

A light emitting layer forming portion is provided on a semiconductor substrate, in which an active layer made of a compound semiconductor is sandwiched between a first and second clad layers made of compound semiconductor having band gap greater than that of the active layer, respectively and having a different conductivity type each other and furthermore a window layer is provided above the second clad layer. The second clad layer is made of a semiconductor having refractive index greater than that of the first clad layer. More preferably the window layer is made of a semiconductor having a refractive index greater than that of the second clad layer. As a result, the absorption of the light emitted from the light emitting layer in the semiconductor substrate can be reduced, and the light can be attracted toward the top surface so that the external quantum efficiency can be advanced.